



ON Semiconductor®

FGA15N120ANTDTU

1200 V, 15 A NPT Trench IGBT

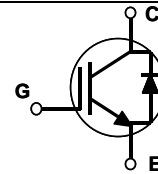
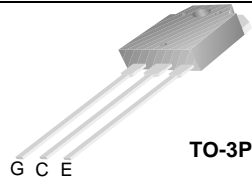
Features

- NPT Trench Technology, Positive temperature coefficient
- Low Saturation Voltage: $V_{CE(sat), typ} = 1.9\text{ V}$
@ $I_C = 15\text{ A}$ and $T_C = 25^\circ\text{C}$
- Low Switching Loss: $E_{off, typ} = 0.6\text{ mJ}$
@ $I_C = 15\text{ A}$ and $T_C = 25^\circ\text{C}$
- Extremely Enhanced Avalanche Capability

Description

Using ON Semiconductor's proprietary trench design and advanced NPT technology, the 1200V NPT IGBT offers superior conduction and switching performances, high avalanche ruggedness and easy parallel operation.

This device is well suited for the resonant or soft switching application such as induction heating, microwave oven.



Absolute Maximum Ratings

Symbol	Description	Ratings	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current	@ $T_C = 25^\circ\text{C}$	30
	Collector Current	@ $T_C = 100^\circ\text{C}$	15
I_{CM}	Pulsed Collector Current (Note 1)	45	A
I_F	Diode Continuous Forward Current	@ $T_C = 25^\circ\text{C}$	30
	Diode Continuous Forward Current	@ $T_C = 100^\circ\text{C}$	15
I_{FM}	Diode Maximum Forward Current	45	A
P_D	Maximum Power Dissipation	@ $T_C = 25^\circ\text{C}$	186
	Maximum Power Dissipation	@ $T_C = 100^\circ\text{C}$	74
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case for IGBT	--	0.67	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case for Diode	--	2.88	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ\text{C/W}$

Notes:

(1) Repetitive rating: Pulse width limited by max. junction temperature

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGA15N120ANTDTU-F109	FGA15N120ANTDTU	TO-3P	Tube	N/A	N/A	30

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
I _{CES}	Collector Cut-Off Current	V _{CE} = V _{CES} , V _{GE} = 0 V	--	--	3	mA
I _{GES}	G-E Leakage Current	V _{GE} = V _{GES} , V _{CE} = 0 V	--	--	± 250	nA
On Characteristics						
V _{GE(th)}	G-E Threshold Voltage	I _C = 15 mA, V _{CE} = V _{GE}	4.5	6.5	8.5	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 15 A, V _{GE} = 15 V	--	1.9	2.4	V
		I _C = 15 A, V _{GE} = 15 V, T _C = 125°C	--	2.2	--	V
		I _C = 30 A, V _{GE} = 15 V	--	2.3	--	V
Dynamic Characteristics						
C _{ies}	Input Capacitance	V _{CE} = 30 V, V _{GE} = 0 V, f = 1 MHz	--	2650	--	pF
C _{oes}	Output Capacitance		--	143	--	pF
C _{res}	Reverse Transfer Capacitance		--	96	--	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{CC} = 600 V, I _C = 15 A, R _G = 10 Ω, V _{GE} = 15 V, Inductive Load, T _C = 25°C	--	15	--	ns
t _r	Rise Time		--	20	--	ns
t _{d(off)}	Turn-Off Delay Time		--	160	--	ns
t _f	Fall Time		--	100	180	ns
E _{on}	Turn-On Switching Loss		--	3	4.5	mJ
E _{off}	Turn-Off Switching Loss		--	0.6	0.9	mJ
E _{ts}	Total Switching Loss		--	3.6	5.4	mJ
t _{d(on)}	Turn-On Delay Time	V _{CC} = 600 V, I _C = 15 A, R _G = 10 Ω, V _{GE} = 15 V, Inductive Load, T _C = 125°C	--	15	--	ns
t _r	Rise Time		--	20	--	ns
t _{d(off)}	Turn-Off Delay Time		--	170	--	ns
t _f	Fall Time		--	150	--	ns
E _{on}	Turn-On Switching Loss		--	3.2	4.8	mJ
E _{off}	Turn-Off Switching Loss		--	0.8	1.2	mJ
E _{ts}	Total Switching Loss		--	4.0	6.0	mJ
Q _g	Total Gate Charge	V _{CE} = 600 V, I _C = 15 A, V _{GE} = 15 V	--	120	180	nC
Q _{ge}	Gate-Emitter Charge		--	16	22	nC
Q _{gc}	Gate-Collector Charge		--	50	65	nC

Electrical Characteristics of DIODE $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
V_{FM}	Diode Forward Voltage	$I_F = 15\text{ A}$	$T_C = 25^\circ\text{C}$	--	1.7	2.7	V
			$T_C = 125^\circ\text{C}$	--	1.8	--	
t_{rr}	Diode Reverse Recovery Time	$I_F = 15\text{ A}$ $di_F/dt = 200\text{ A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	--	210	330	ns
			$T_C = 125^\circ\text{C}$	--	280	--	
I_{rr}	Diode Peak Reverse Recovery Current		$T_C = 25^\circ\text{C}$	--	27	40	A
			$T_C = 125^\circ\text{C}$	--	31	--	
Q_{rr}	Diode Reverse Recovery Charge		$T_C = 25^\circ\text{C}$	--	2835	6600	nC
			$T_C = 125^\circ\text{C}$	--	4340	--	

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

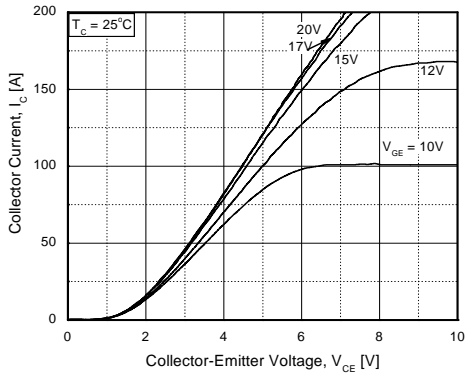


Figure 2. Typical Saturation Voltage Characteristics

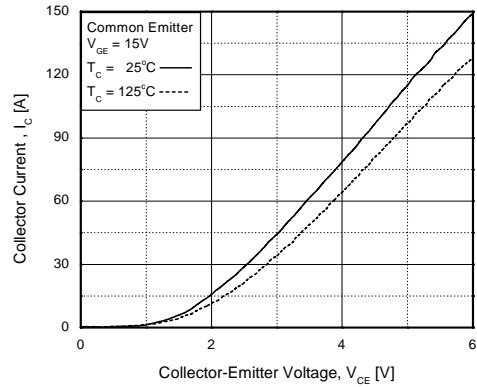


Figure 3. Saturation Voltage vs. Case Temperature at Variant Current Level

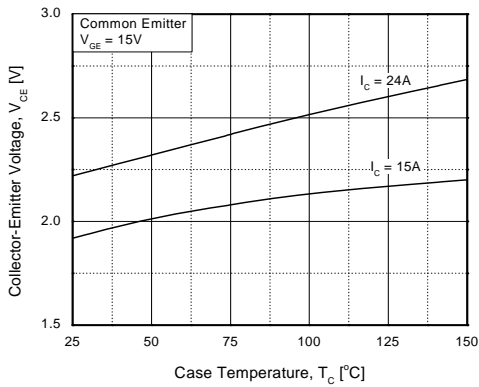


Figure 4. Saturation Voltage vs. V_GE

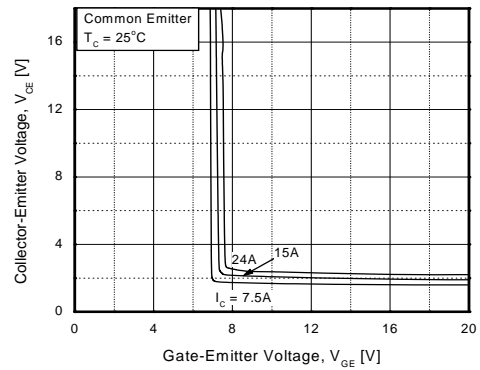


Figure 5. Saturation Voltage vs. V_GE

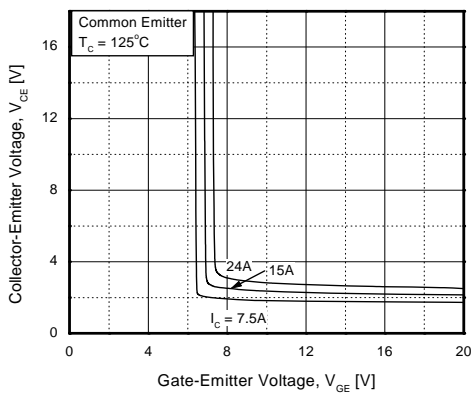
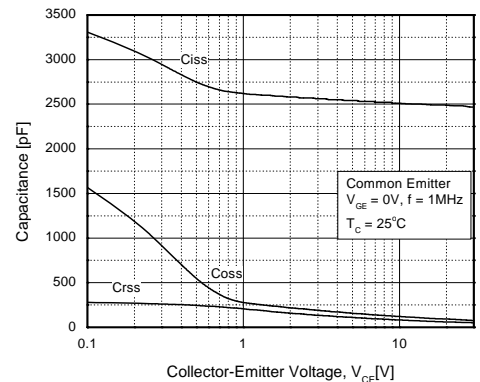


Figure 6. Capacitance Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Turn-On Characteristics vs. Gate Resistance

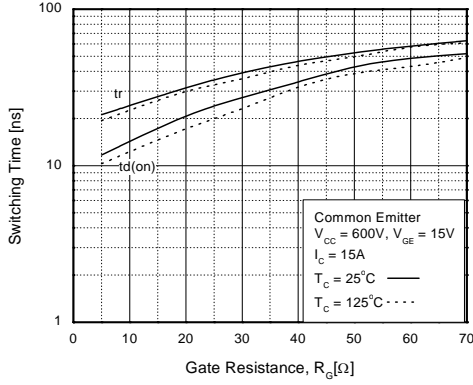


Figure 8. Turn-Off Characteristics vs. Gate Resistance

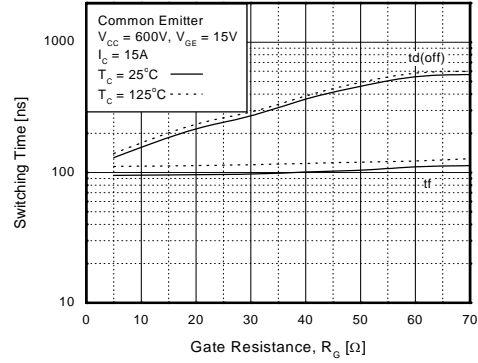


Figure 9. Switching Loss vs. Gate Resistance

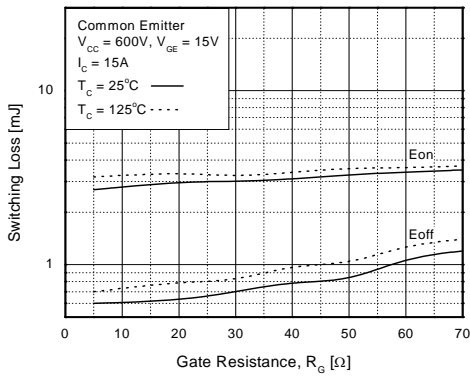


Figure 10. Turn-On Characteristics vs. Collector Current

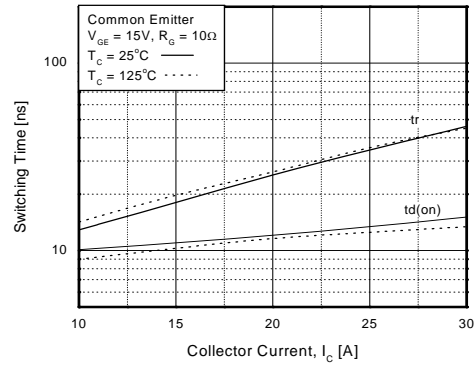


Figure 11. Turn-Off Characteristics vs. Collector Current

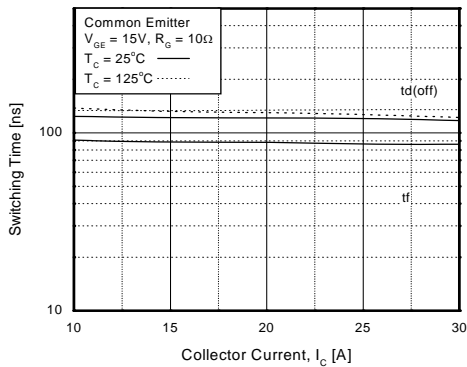
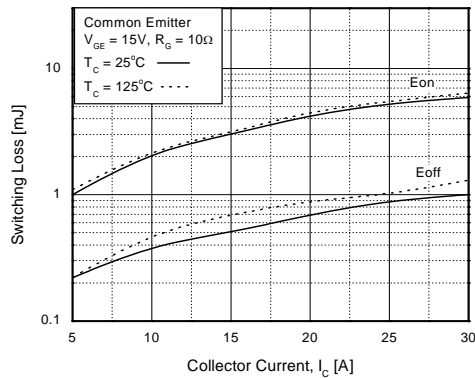


Figure 12. Switching Loss vs. Collector Current



Typical Performance Characteristics (Continued)

Figure 13. Gate Charge Characteristics

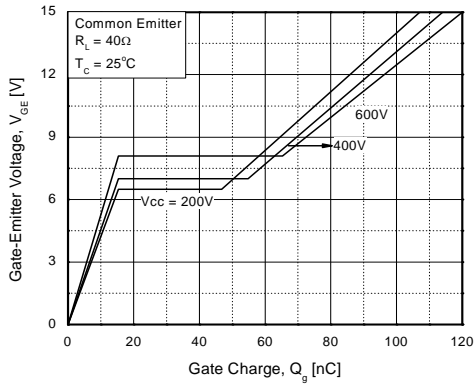


Figure 14. SOA Characteristics

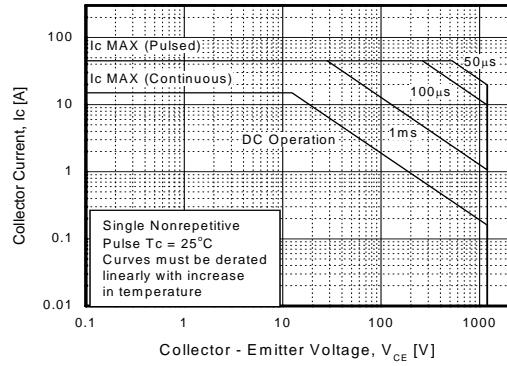


Figure 15. Turn-Off SOA

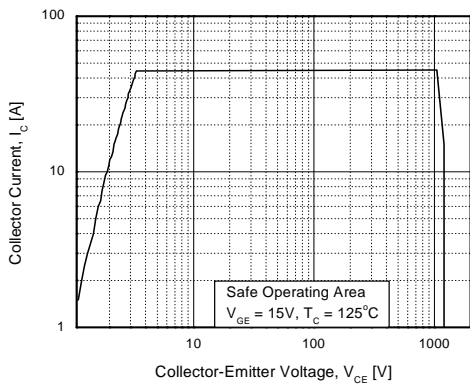
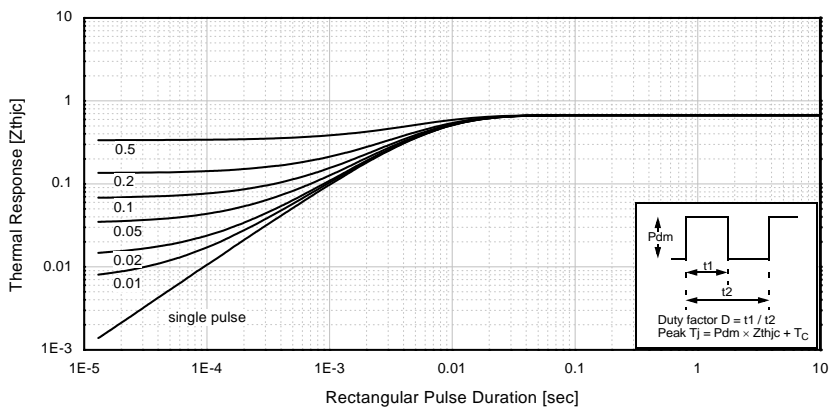


Figure 16. Transient Thermal Impedance of IGBT



Typical Performance Characteristics (Continued)

Figure 17. Forward Characteristics

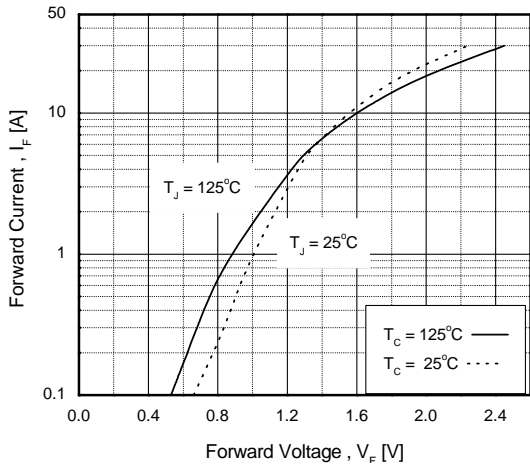


Figure 18. Reverse Recovery Current

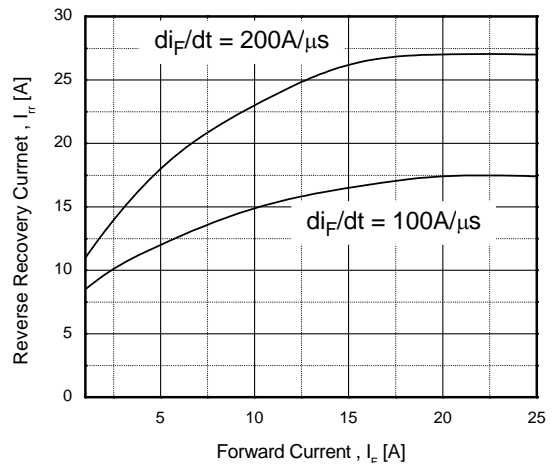


Figure 19. Stored Charge

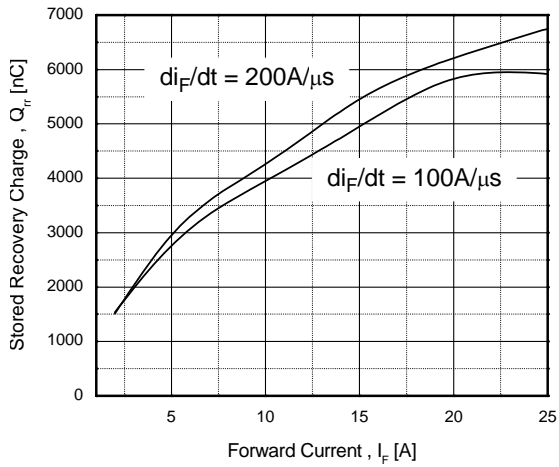
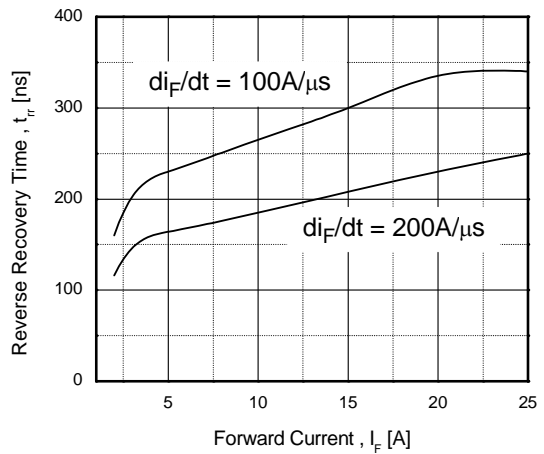


Figure 20. Reverse Recovery Time



Mechanical Dimensions

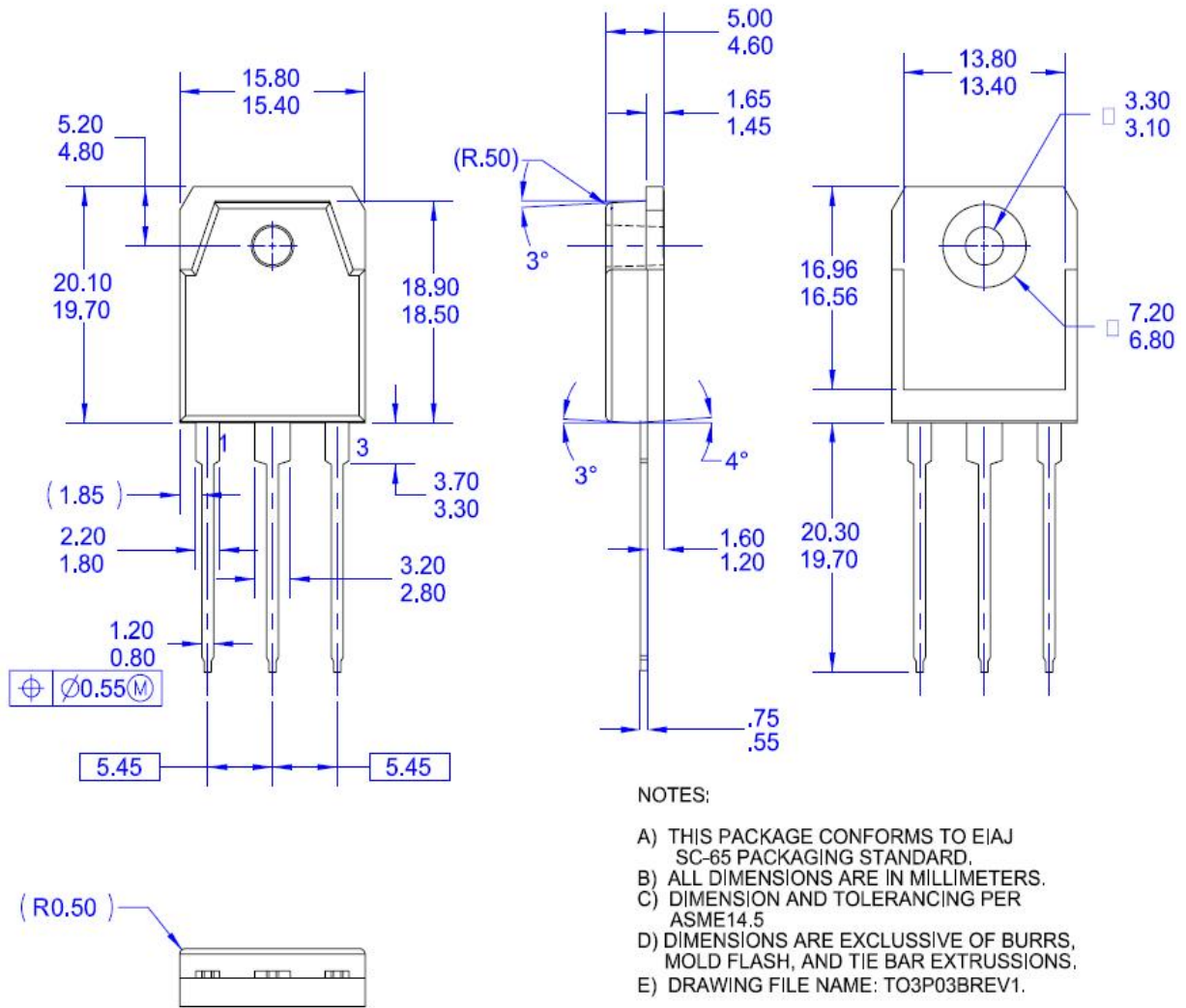


Figure 21. TO-3P 3L - 3LD, T03, PLASTIC, EIAJ SC-65

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